



# STB50NE10L

## N - CHANNEL 100V - 0.020Ω - 50A - D<sup>2</sup>PAK STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB50NE10L	100 V	<0.025 Ω	50 A

- TYPICAL R<sub>DS(on)</sub> = 0.020 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE AT 100 °C
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

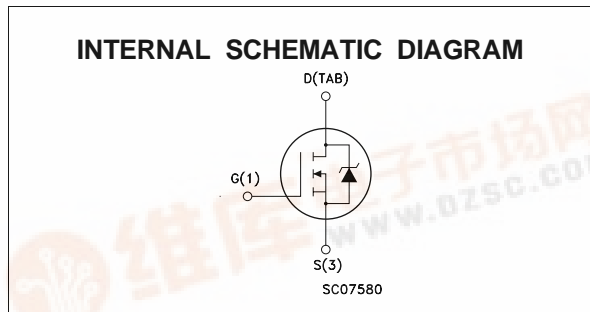
- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	100	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	50	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	35	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	200	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	6	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 50 A, di/dt ≤ 300 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>



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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5	°C/W
T <sub>j</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	50	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	300	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	1	1.7	2.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 25 A V <sub>GS</sub> = 5 V I <sub>D</sub> = 25 A		0.020 00.24	0.025 0.030	mΩ μΩ
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	50			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 25 A	20	35		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		TBD	TBD	pF pF pF

**ELECTRICAL CHARACTERISTICS** (continued)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 25\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		TBD	TBD	ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 50\text{ A}$ $V_{GS} = 10\text{ V}$		TBD	TBD	nC nC nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 80\text{ V}$ $I_D = 50\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		TBD	TBD	ns ns ns

## SOURCE DRAIN DIODE

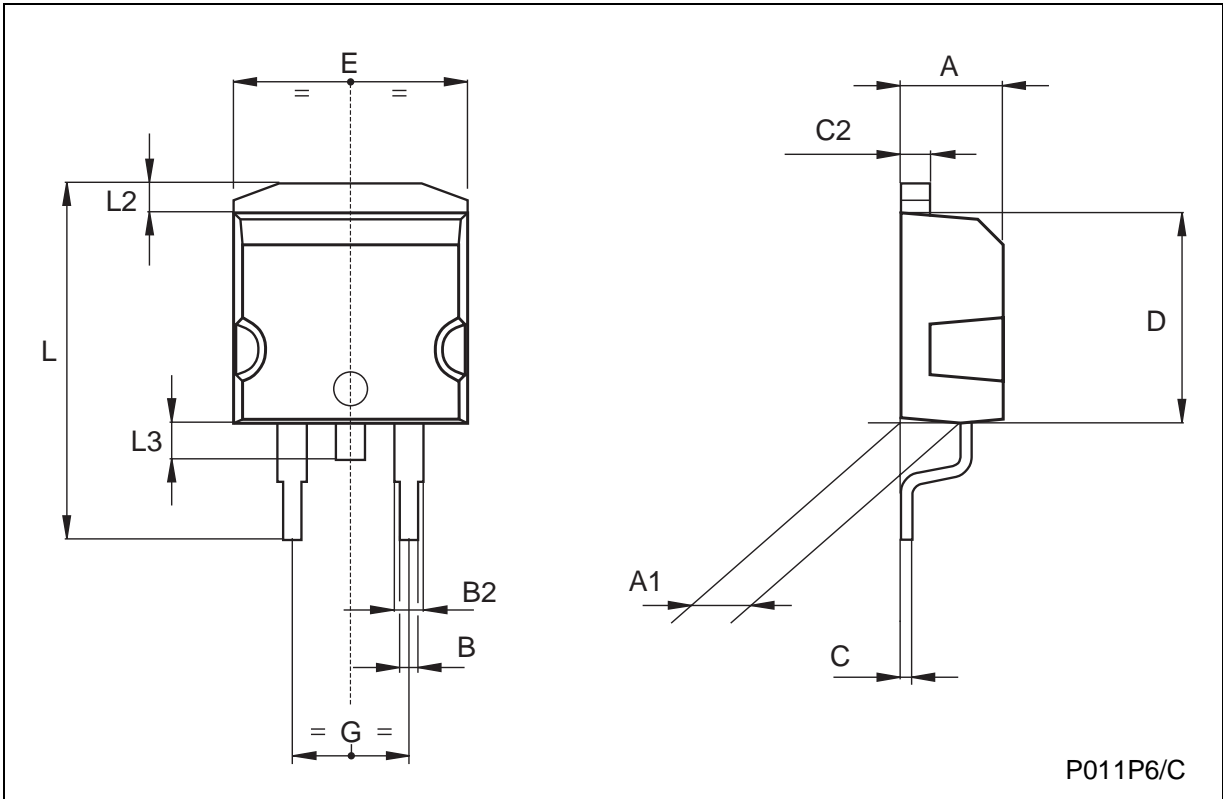
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				50	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				200	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 50\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 50\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		TBD		ns
$Q_{rr}$	Reverse Recovery Charge					nC
$I_{RRM}$	Reverse Recovery Current					A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

**TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.25		1.4	0.049		0.055
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.28	0.393		0.404
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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